

DATASHEET

TO-247-TSC 1200V N-Channel Enhancement SiC Power MOSFET

EL-MAKR04120PA-TC



V _{DSS}	=	1200	٧
I _D	=	55	Α
R _{DS(on)}	=	40 r	mΩ

Preliminary

Features

- High Blocking Voltage with Low On-Resistance
- Low gate resistance for high-frequency switching
- Low capacitances and low gate charge
- Best thermal conductivity and behavior
- Pb-Free Lead, Halogen Free, RoHS Compliant





Schematic

Pin Configuration

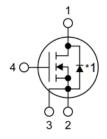
- 1. Drain
- 2. Power Source
- 3. Driver Source
- 4. Gate
- *1. Body Diode

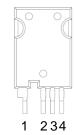
Benefits

- Improve System Efficiency
- Increase Power Density
- Reduce Heat Sink Requirement
- Reduction of System Cost

Applications

- Solar Inverters
- EV Battery Chargers
- High Voltage DC/DC Converters
- Switch Mode Power Supply





Key Performance Parameters

Symbol	V_{DSmin}	V_{GSS}	Ι _D	I _{DP}	$T_{J,max}$	P _D
Parameter	Drain-Source Voltage	Gate-Source Voltage (DC)	Continuous Drain Current	Pulse Drain Current	Junction temperature	Power Dissipation
Value	1200V	-4/18V	55A	171A	175 °C	454W



Maximum Ratings

Parameter	Symbol	Value	Unit	Test Conditions
Drain - Source Voltage	V_{DSmin}	1200	V	V _{GS} = 0V, I _D = 250μA
Gate - Source Voltage (DC) Max	V_{GS}	-10 / +20	V	
Gate - Source Voltage (DC)	V_{GS}	-4 / +18	V	Recommended operating values
Continuous Drain Current	L_ *2	55		V _{GS} =20V, T _C =25°C
Continuous Drain Current	l _D *2	39	A	V _{GS} =20V, T _C =100°C
Pulsed Drain Current	IDP	171	А	
Power Dissipation	P _D *3	454	W	
Operating Junction	TJ	175	°C	
Storage Temperature	T _{stg}	-55 to +175	°C	
Solder Temperature	TL	260	°C	
Mounting Torque	M _d	1 8.8	Nm lbf-in	M3 or 6-32 screw

^{*1} Please be advised not to use SiC-MOSFETs with V_{GS} below 12V as doing so may cause thermal runaway.

^{*2} Limited by maximum Ta and for Max. R_{thJC}

^{*3} $P_W \le 10\mu s$, Duty cycle $\le 1\%$

^{*4} Tested after applying V_{GS} for 100ms.

^{*5} Pulsed



Electrical Characteristics

Darameter	Symbol	Value			Unit	Test Conditions	
Parameter	Symbol	Min	Тур	Max	Onn	rest Conditions	
Drain-Source Breakdown Voltage	V _{(BR)DSS}	1200	-	-	V	V _{GS} = 0V, I _D = 250μA	
Gate Threshold Voltage	V _{GS(th)} *4	-	2.8	-	V	V _{GS} =V _{DS} , I _D =2mA	
Zero Gate Voltage Drain Current	I_{DSS}	-	1	-	μA	V _{DS} = 1200V, V _{GS} = 0V	
Gate-Source Leakage Current	I _{GSS+}	-	10	200	nA	V _{GS} = 20V, V _{DS} = 0V	
Drain-Source	D *5	-	40	60	m0	V _{GS} = 18V, I _D = 24A	
On-State Resistance	R _{DS(on)} *5	-	68	100	mΩ	V _{GS} = 18V, I _D = 24A,T _J = 175°C	
Input Capacitance	C _{iss}	-	2910	-			
Output Capacitance	C_{oss}	-	103	-	pF	V _{GS} = 0V V _{DS} = 800V f= 1MHz	
Reverse Transfer Capacitance	C_{rss}	-	10	-		I— 11VII IZ	
Turn-On Delay Time	t _{d(on)}	-	50	-			
Rise Time	t _r	-	20	-		V _{DS} =800V I _D =24A	
Turn-Off Delay Time	t _{d(off)}	-	45	-	ns	V_{GS} =-4V/+18V R_G =2.5 Ω	
Fall Time	t _f	-	10	-			
Gate to Source Charge	Q_gs	-	40	-			
Gate to Drain Charge	Q_{gd}	-	29	-	nC	V_{DS} = 800V I_{DS} = 24A V_{GS} = +18V/-4V	
Total Gate Charge	Qg	-	115	-		100 1007 10	
Gate resistance	R_G	-	1	-	Ω	f=1MHz, V _{AC} =25mV	



Body Diode Characteristics

Parameter	Symbol	Value		Unit	Test Conditions	
r ai ailletei	rameter Symbol -		Max.	Offic		
Diode Forward Voltage	V_{SD}	4.6	-	V	V _{GS} = -4V, I _S = 24A	
Continuous Diode Forward Current	I _S	-	40	А		

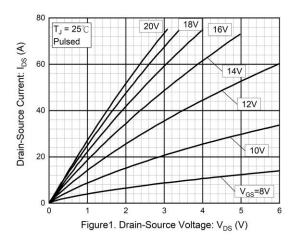
Thermal Characteristics (Measured conformable to JESD51-14.)

Parameter	Symbol	Value		Unit
r arameter	Symbol	Тур	Max	Oilit
Thermal Resistance from Junction to Case	Rejc	0.26	0.33	°C/W

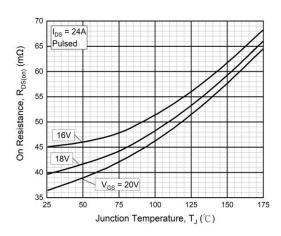


Typical Performance

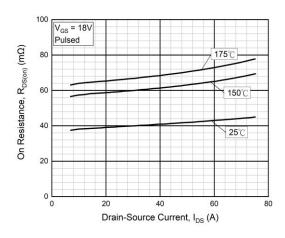
Typical Output Characteristics (I)



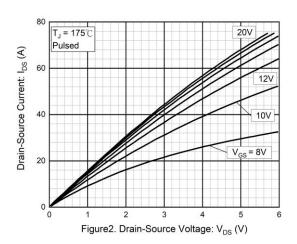
Typical on-resistance by various junction temperature and gate voltage



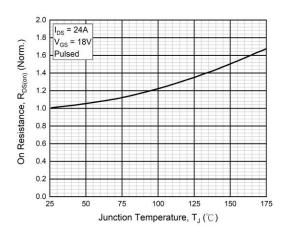
Typical on-resistance by various drain current and junction temperature



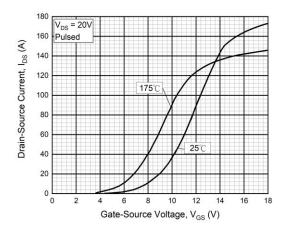
Typical Output Characteristics(II)



Normalized on-resistance by various junction temperature

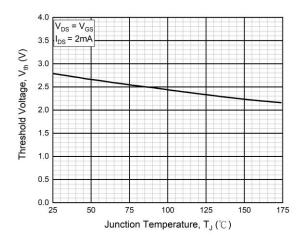


Typical transfer characteristics by various gate voltage and junction temperature



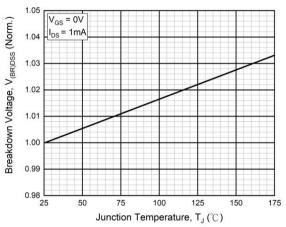


Typical threshold voltage by various junction temperature

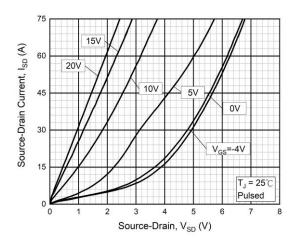


junction temperature

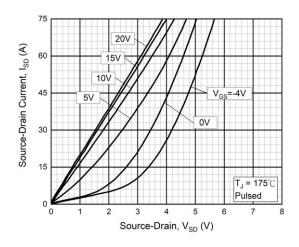
Normalized breakdown voltage by various



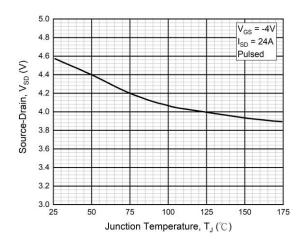
Typical body diode forward current by various forward voltage and gate voltage(I)



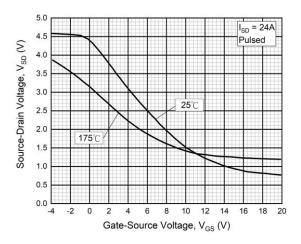
Typical body diode forward current by various forward voltage and gate voltage(II)



Typical body diode forward voltage by various junction temperature

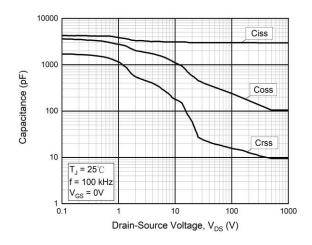


Typical body diode forward voltage by various gate voltage and junction temperature

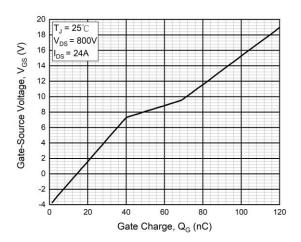




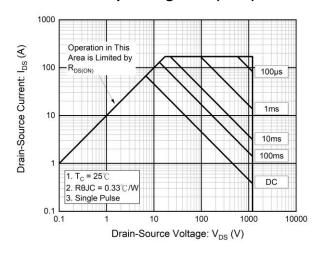
Typical capacitance by various drain voltage



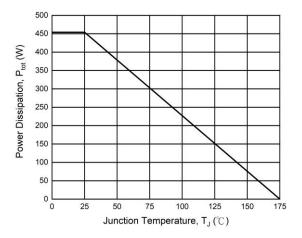
Typical gate charge characteristic



Maximum Safe Operating Area (SOA)

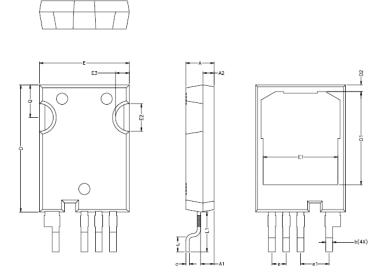


Power dissipation vs. Junction Temperature





Package Outlines



MILLIMETERS DIM TYP. MAXMIN 5.02 5.22 Α 4.82 2.61 Α1 2.21 2.41 Α2 2.2 1.8 1.2 b 0.95 1.45 0.35 0.85 0.6 22.34 22.54 22.74 D D1 16.3 16.55 16.8 D2 0.99 1.19 1.39 Е 15.74 15.94 16.14 E1 13.01 13.26 13.51 E2 4.71 4.91 5.11 E3 2.26 2.46 2.66 2.54BSC. е 5.08BSC. e1 L L1 Q 5.59 5.79 5.99

Unit: mm

Drawing and Dimensions

DATASHEET TO-247-TSC 1200V N-Channel Enhancement SiC Power MOSFET EL-MAKR04120PA-TC (Preliminary)



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